

Silicon NPN Power Transistors

MJF13007

DESCRIPTION

- With TO-220F package
- High voltage ,high speed

APPLICATIONS

- Particularly suited for 115V and 220V switchmode applications such as switching regulators,inverters ,motor controls,solenoid/ relay drivers and deflection circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

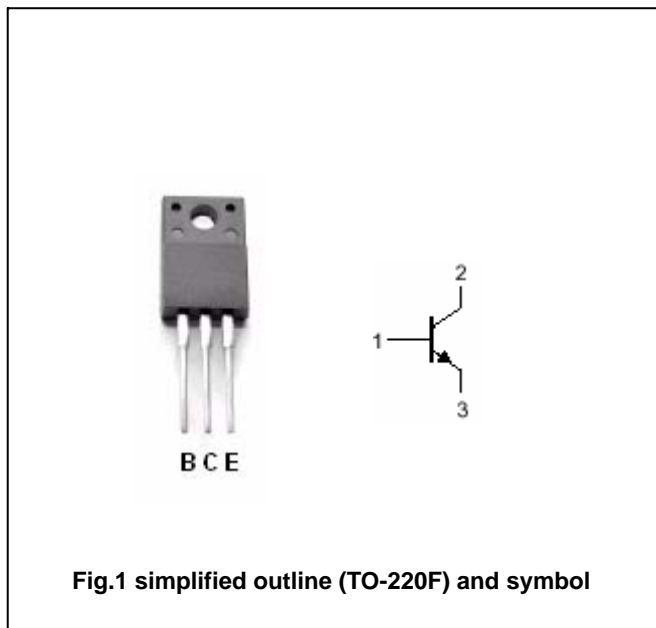


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings(Tc=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	700	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	9	V
$I_C$	Collector current (DC)		8	A
$I_{CM}$	Collector current-Peak		16	A
$I_B$	Base current		4	A
$I_{BM}$	Base current-Peak		8	A
$I_E$	Emitter current		12	A
$I_{EM}$	Emitter current-Peak		24	A
$P_D$	Total power dissipation	$T_C=25$	40	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th j-c}$	Thermal resistance from junction to case	3.12	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	400			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			1.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =1.0A T <sub>C</sub> =100			2.0 3.0	V
V <sub>CEsat-3</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2.0A			3.0	V
V <sub>BEsat-1</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			1.2	V
V <sub>BEsat-2</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =1.0A T <sub>C</sub> =100			1.6 1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =700V; I <sub>E</sub> =0 T <sub>C</sub> =125			0.1 1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =9V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =2A; V <sub>CE</sub> =5V	8		40	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A; V <sub>CE</sub> =5V	5		30	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CE</sub> =10V; f=1MHz	4			MHz
C <sub>OB</sub>	Collector outoput capacitance	I <sub>E</sub> =0; f=0.1MHz; V <sub>CB</sub> =10V		80		pF

## Switching times resistive load

t <sub>d</sub>	Delay time	V <sub>CC</sub> =125V, I <sub>C</sub> =5A I <sub>B1</sub> =-I <sub>B2</sub> =1.0A t <sub>p</sub> =25 μs duty cycle 1%			0.1	μs
t <sub>r</sub>	Rise time				1.5	μs
t <sub>s</sub>	Storage time				3.0	μs
t <sub>f</sub>	Fall time				0.7	μs

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PACKAGE OUTLINE

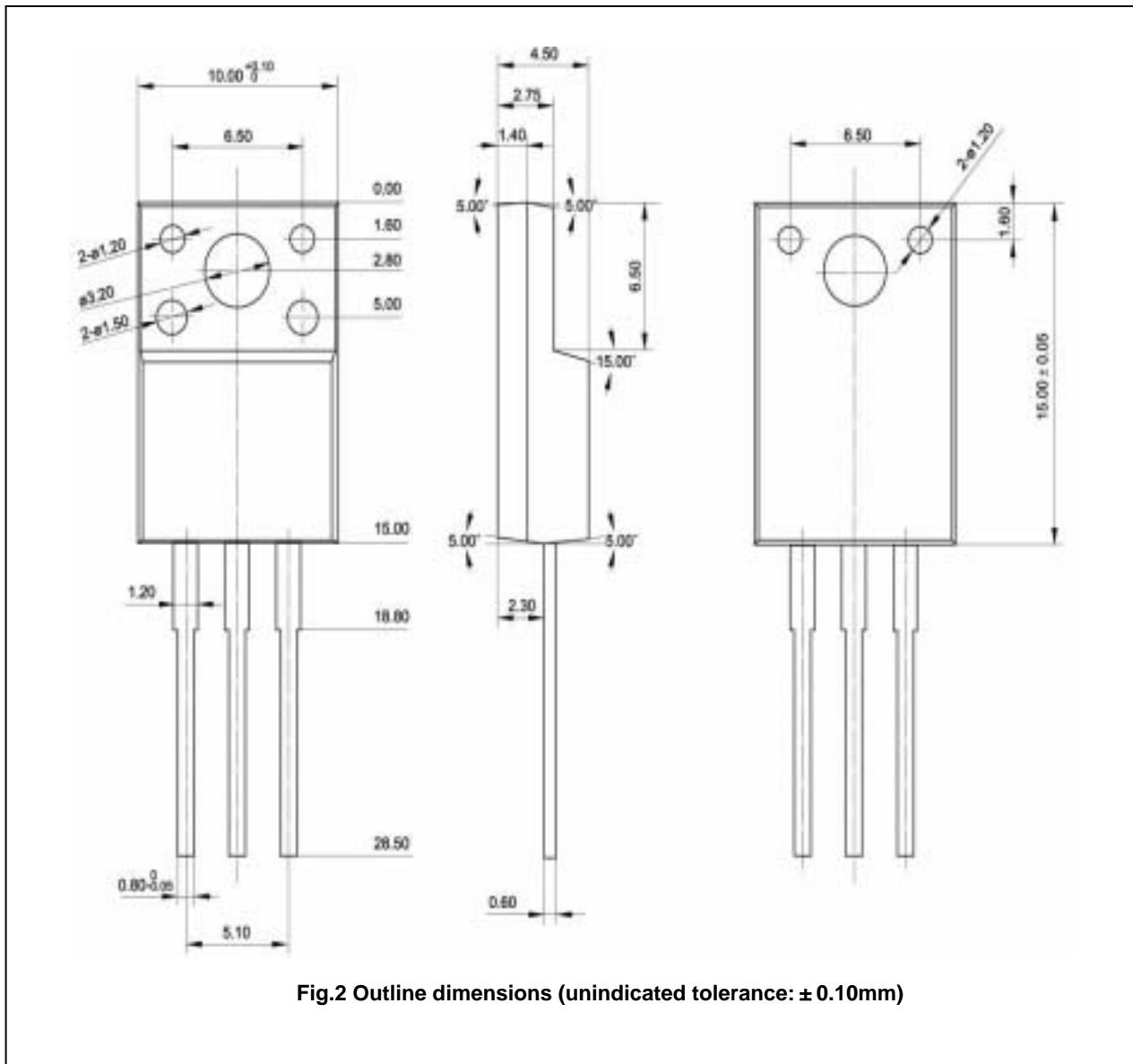


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10mm)

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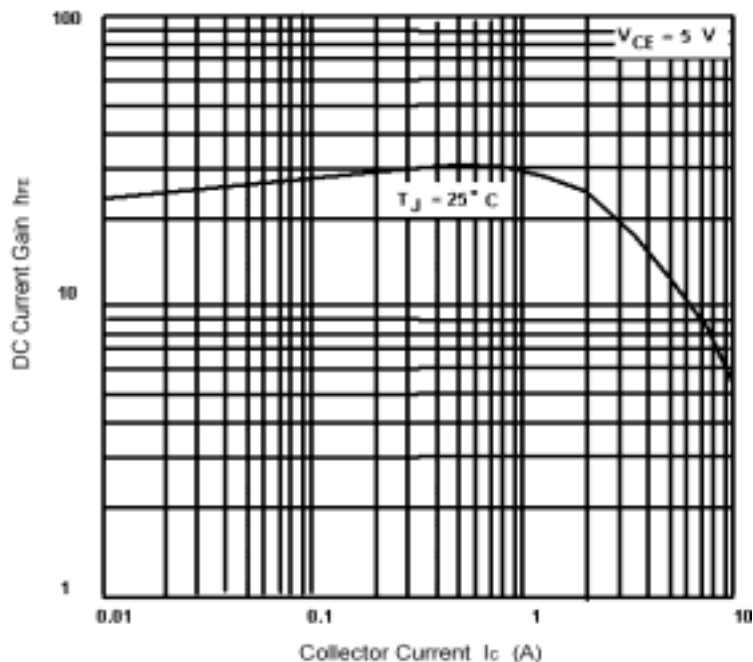


Fig.3 DC current Gain

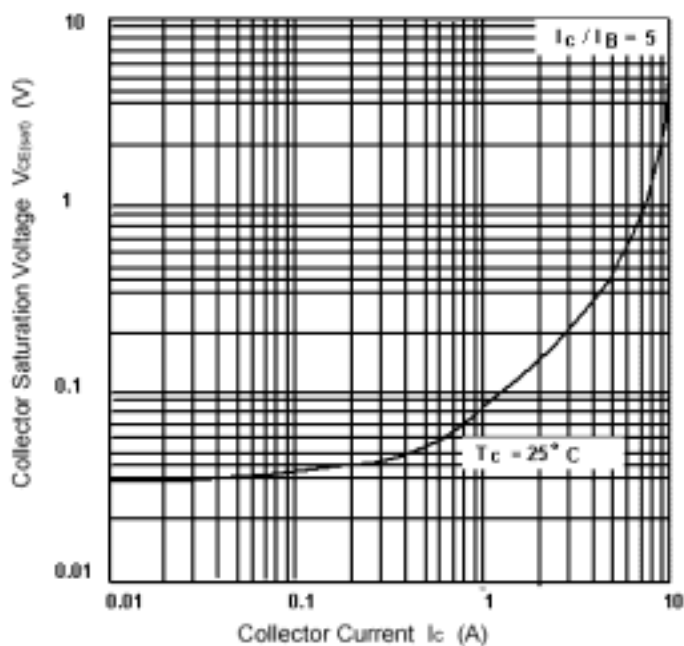


Fig.4 Collector-Emitter Saturation Voltage

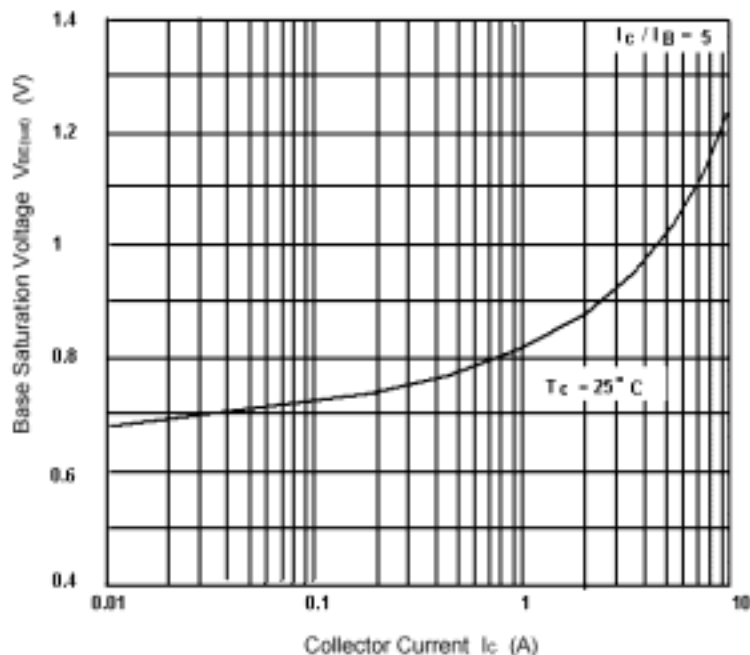


Fig.5 Base-Emitter Saturation Voltage

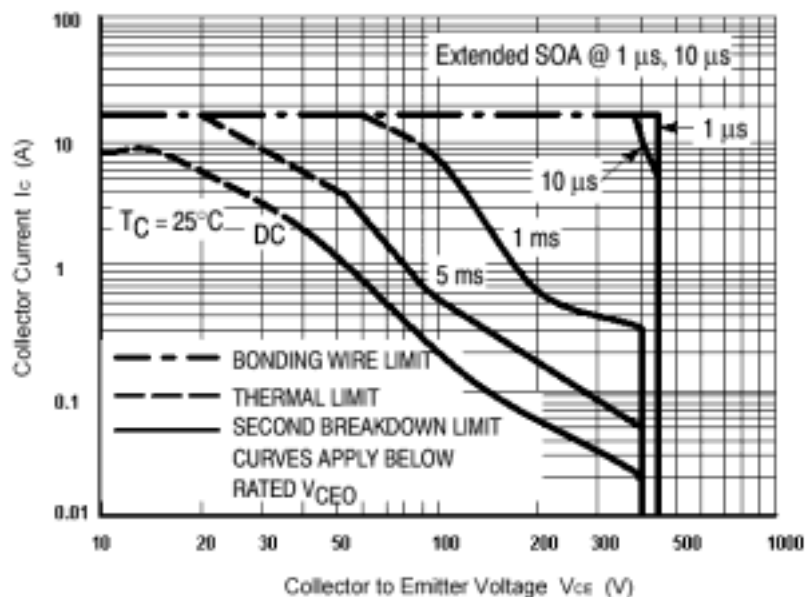


Fig.6 Safe Operating Area